Maximum Ratings @T_A = 25°C unless otherwise specified

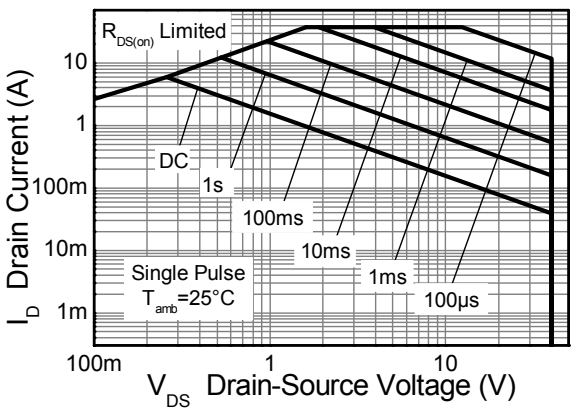
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	40	V
Gate-Source voltage		(Note 2)	V_{GS}	±20	V
Continuous Drain current	V_{GS} = 10V	(Note 4)	I_D	8.0	A
		T_A = 70°C (Note 4)		6.5	
		(Note 3)		6.0	
Pulsed Drain current	V_{GS}= 10V	(Note 5)	I_{DM}	37	A
Continuous Source current (Body diode)		(Note 4)	I_S	4.2	A
Pulsed Source current (Body diode)		(Note 5)	I_{SM}	37	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

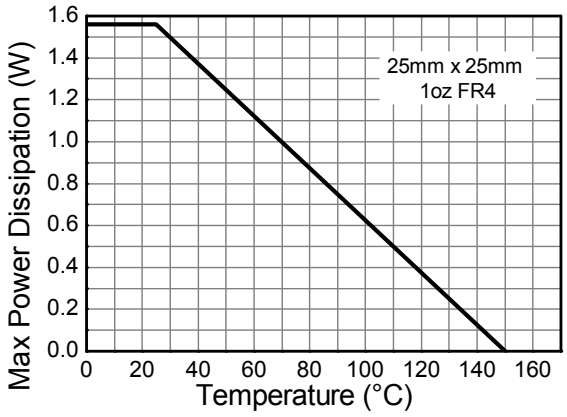
Characteristic		Symbol	Value	Unit
Power dissipation	(Note 3)	P_D	1.56	W
Linear derating factor			12.5	mW/°C
	(Note 4)		2.8	W
			22.5	mW/°C
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{\theta JA}$	80	°C/W
	(Note 4)		44.5	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	35	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	°C

Notes:
2. AEC-Q101 V_{GS} maximum is ±16V.
3. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
4. Same as note (3), except the device is measured at t ≤ 10 sec.
5. Same as note (3), except the device is pulsed with D= 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
6. Thermal resistance from junction to solder-point (at the end of the drain lead).

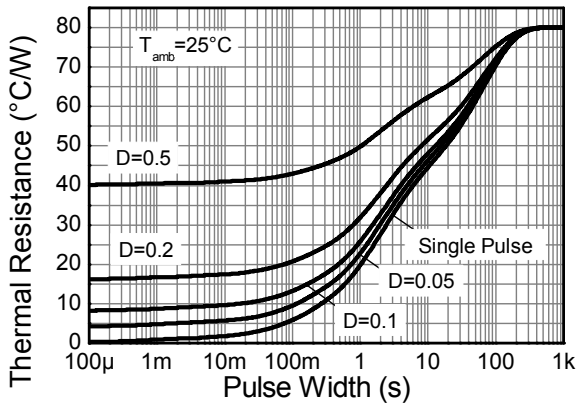
Thermal Characteristics



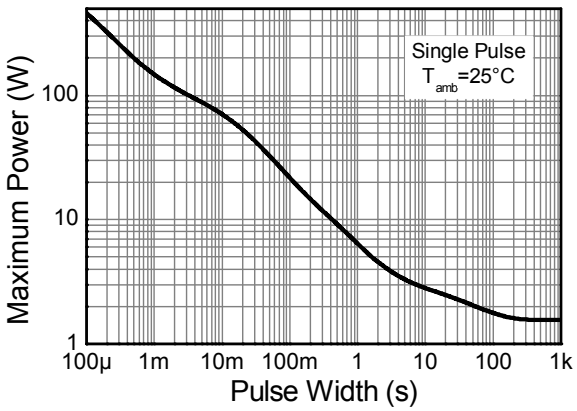
Safe Operating Area



Derating Curve



Transient Thermal Impedance



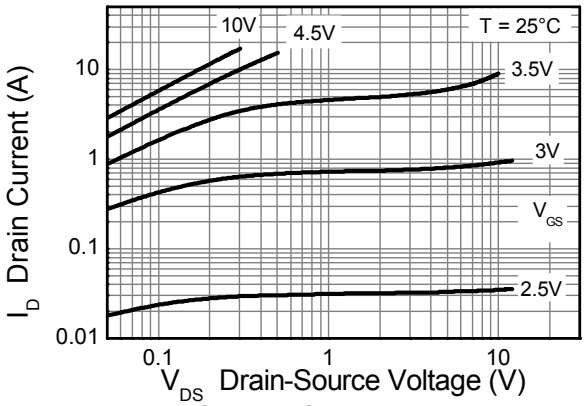
Pulse Power Dissipation

Electrical Characteristics @T_A = 25°C unless otherwise specified

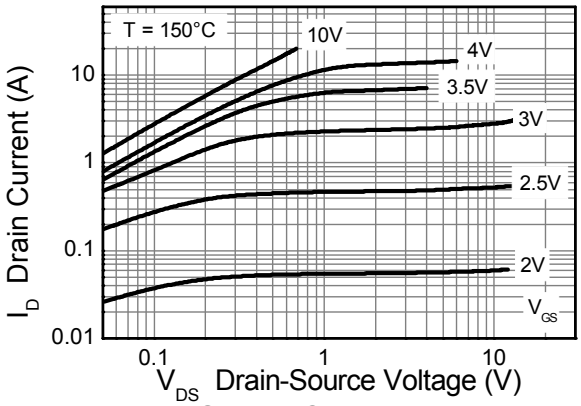
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	I_D = 250μA, V_{GS}= 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.5	μA	V_{DS}= 40V, V_{GS}= 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS}= ±20V, V_{DS}= 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	I_D= 250μA, V_{DS}= V_{GS}
Static Drain-Source On-Resistance (Note 7)	$R_{DS\ (ON)}$	—	0.017	0.027	Ω	V_{GS}= 10V, I_D= 7A
			0.031	0.047		V_{GS}= 4.5V, I_D= 6A
Forward Transconductance (Notes 7 & 8)	g_{fs}	—	22.8	—	S	V_{DS}= 15V, I_D= 7A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.85	1.1	V	I_S= 7A, V_{GS}= 0V
Reverse recovery time (Note 8)	t_{rr}		12.2	—	ns	I_S= 2.5, di/dt= 100A/μs
Reverse recovery charge (Note 8)	Q_{rr}	—	5.4	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	604	—	pF	V_{DS}= 20V, V_{GS}= 0V f= 1MHz
Output Capacitance	C_{oss}	—	106	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	59.6	—	pF	
Total Gate Charge (Note 9)	Q_g	—	6.3	—	nC	V_{GS}= 4.5V
Total Gate Charge (Note 9)	Q_g	—	12.9	—	nC	V_{GS}= 10V V_{DS}= 20V I_D= 7A
Gate-Source Charge (Note 9)	Q_{gs}	—	2.4	—	nC	
Gate-Drain Charge (Note 9)	Q_{gd}	—	3	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	—	3.1	—	ns	V_{DD}= 20V, V_{GS}= 10V I_D= 1A, $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 9)	t_r	—	3.1	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	—	15.4	—	ns	
Turn-Off Fall Time (Note 9)	t_f	—	7.5	—	ns	

Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
8. For design aid only, not subject to production testing.
9. Switching characteristics are independent of operating junction temperatures.

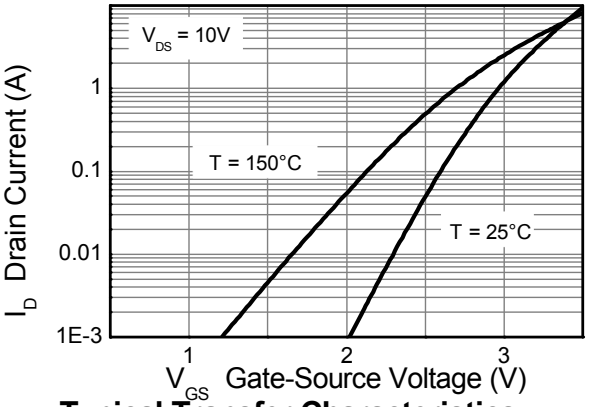
Typical Characteristics



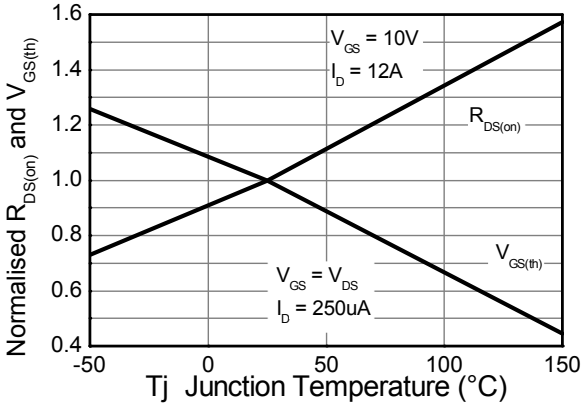
Output Characteristics



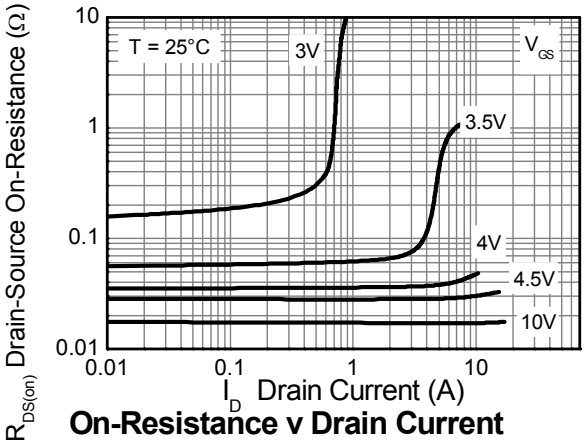
Output Characteristics



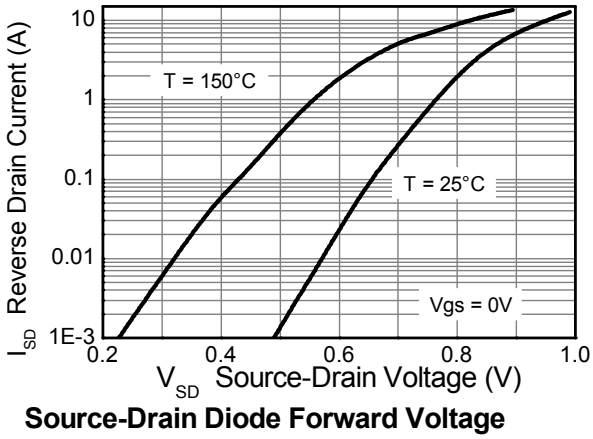
Typical Transfer Characteristics



Normalised Curves v Temperature

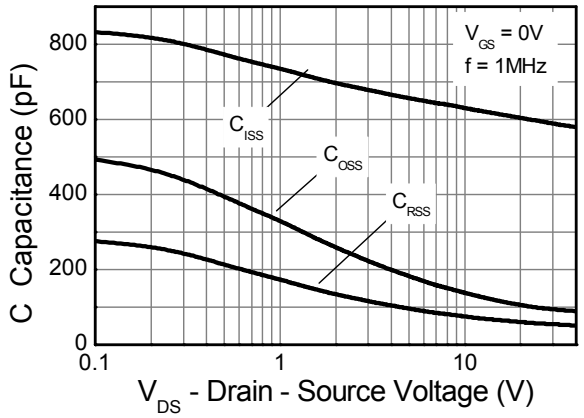


On-Resistance v Drain Current

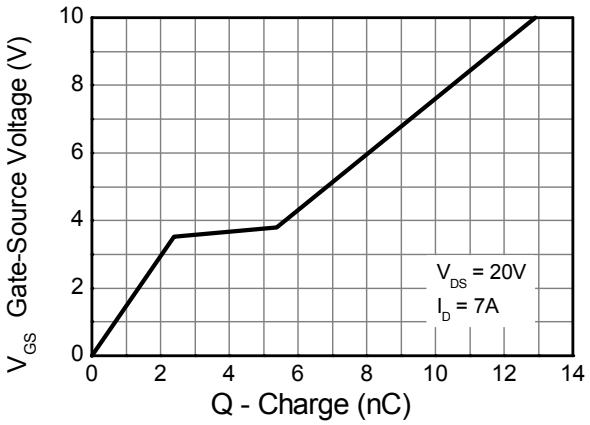


Source-Drain Diode Forward Voltage

Typical Characteristics - continued

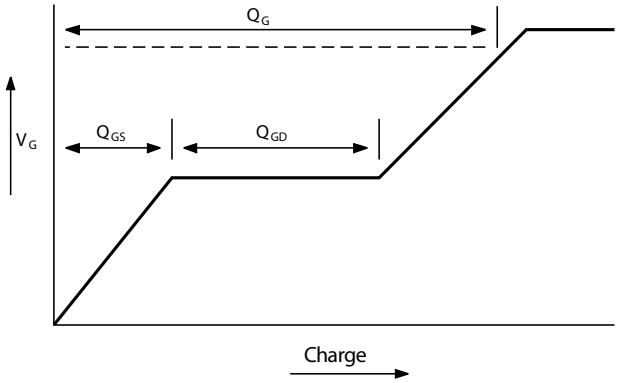


Capacitance v Drain-Source Voltage

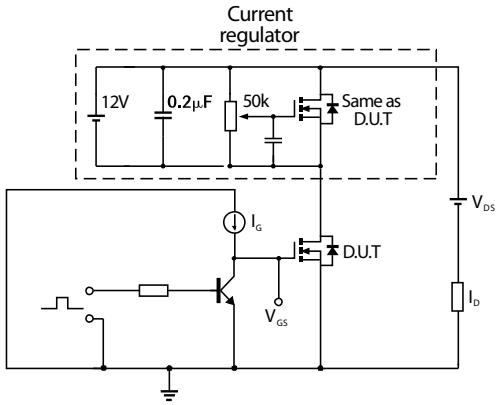


Gate-Source Voltage v Gate Charge

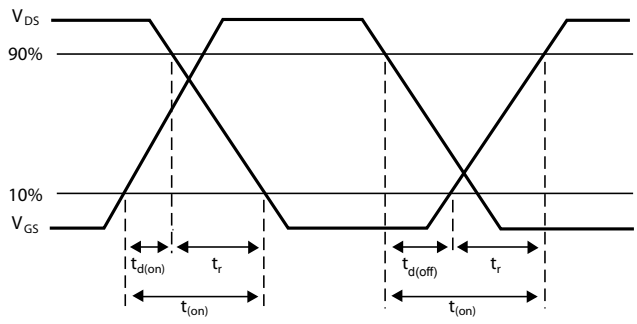
Test Circuits



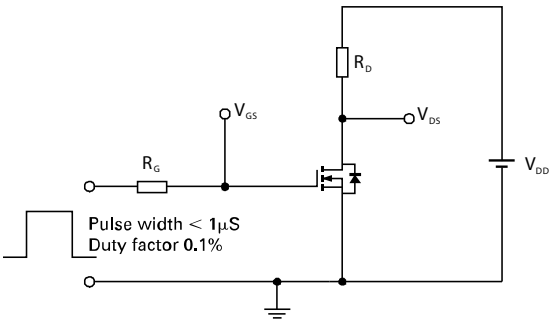
Basic gate charge waveform



Gate charge test circuit

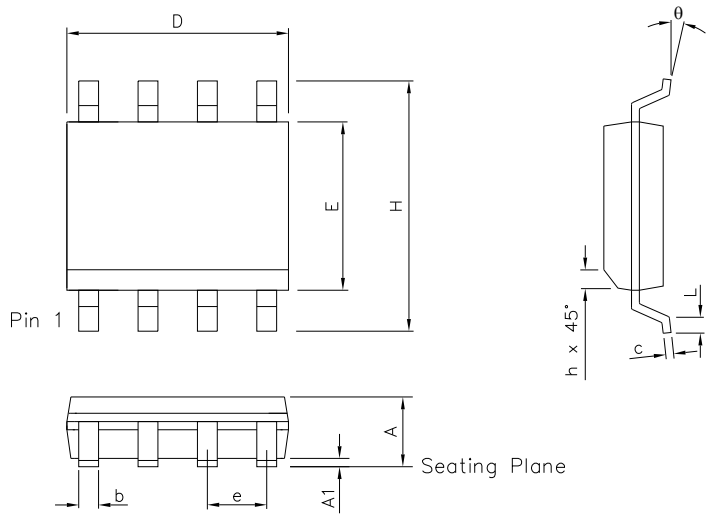


Switching time waveforms



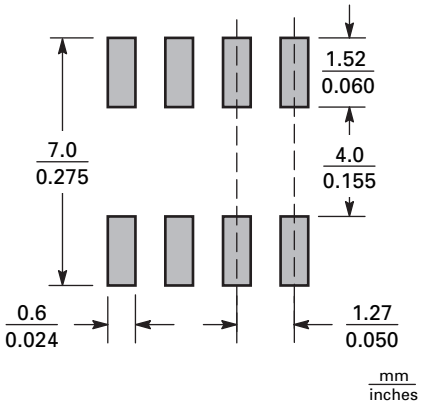
Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Suggested Pad Layout



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